

Unleash Innovation

N3E FB29 V0.5 MB-Latch Optimization

SCLD/DTP/TSMC 2022/03/15

Serial number: 202203171623-2654593

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N3E FB29 V0.5 MB-Latch Optimization

- Two feedback from customer regarding N3E MB-Latch: Leakage and MPW
 - MPW is due to strong layout effect on critical 1fin device; increasing clock size won't help



	Nodo	Coll	sim va	lue(ns)	D:4
	Node	Cell	Corner	3 Sigma	Bit
4	N3E	MB8LHQ_NOM4222_D1_143MH286	0.375	1.204	Q1
1	N3E	MB8LHQ_NOM <mark>4422</mark> _D1_143MH286	0.316	1.171	Q1

RC: Qcap C651 benchmark

Model N3E: cln3e_1d2_sp_v0d5_2p1_for_C651_usage.l

- -Timing slew:INVDx-predriver, -cload: INVDx-FO4 @ SSGNP/0.48V/m25c for MPW
- -Timing slew:INVDx-predriver, -cload: INVDx-FO4 @ SSGNP/0.5V/m25c for PP.
- -power slew: INVDx-predriver, -cload: 0.001fF @ FFGNP/0.75V/85C

Leakage is also due to CPO-related layout effect

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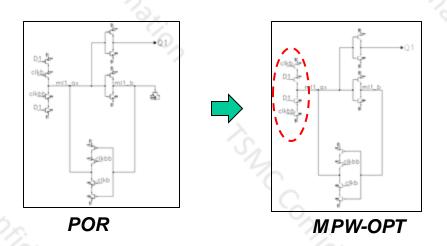
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- Leakage Optimization
 - Change CPO location on 1st stage PMOS (at the cost of speed)

0,			N3E	POR				, C	N3E (LLKG)		Ratio (LLKG/POR)				
ULVT	Setup AVG(ps)	CP2Q AVG(ps)	Speed (GHz)	Pwr-10% (uW)	Leakage (nW)	Area (CPP)	Setup AVG(ps)	CP2Q AVG(ps)	Speed (GHz)	Pwr-10% (uW)	Leakage (nW)	Area (CPP)	Speed	Power	Leakage	Area
MB4LHQ_NOM4222_D1_143MH286	21.7	61.1	12.1	2.1	586.3	20	25.4	63.7	11.2	2.0	465.9	20	-7.07%	-2.21%	-20.54%	0
MB6LHQ_NOM4222_D1_143MH286	19.8	67.5	11.5	2.8	821.8	30	23.4	70.0	10.7	2.7	641.2	30	-6.53%	-2.40%	-21.98%	0
MB8LHQ_NOM4222_D1_143MH286	18.0	73.8	10.9	3.5	1057.4	40	21.5	76.3	10.2	3.5	816.5	40	-6.19%	-2.59%	-22.78%	0

MPW Optimization

Do stack swapping and remove CPO (completely)



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PPA Comparison

- The leakage-opt version shows speed/leakage trade-off; however, no change on mpw-critical device (no mpw improvement)
- The mpw-opt version shows more speed degradation; however, both mpw and leakage got improved
- Suggest to take mpw-opt version as a replacement of POR (not footprint compatible) or as an addition

	7/	-	N3E	POR				7//	N3E (L	KG Opt)				, N;	BE(MPW O	pt)		Ra	tio (LKG	Ratio (MPW Opt/N3E POR)				
ULVT	Setup AVG(ps)	CP2Q AVG(ps)	Speed (GHz)	Pwr-10% (uW)	Leakage (nW)	Area (CPP)	Setup AVG(ps)	CP2Q AVG(ps)		Pwr-10% (uW)	Leakage (nW)	Area (CPP)	Setup AVG(ps)	CP2Q AVG(ps)		Pwr-10% (uW)	Leak age (nW)	Speed	Power	Leakage	Area	Speed	Power	Leakage
MB4LHQ_NOM4222_D1_143MH286	21.7	61.1	12.1	2.1	586.3	20	25.4	63.7	11.2	2.0	465.9	20	24.46	65.73	11.09	1.81	267.38	-7.07%	-2.21%	-20.54%	0	-8.35%	-13.81%	-54.40%
MB6LHQ_NOM4222_D1_143MH286	19.8	67.5	11.5	2.8	821.8	30	23.4	70.0	10.7	2.7	641.2	30	22.73	72.32	10.52	2.44	366.46	-6.53%	-2.40%	-21.98%	0	-8.52%	-12.86%	-55.41%
MB8LHQ_NOM4222_D1_143MH286	18.0	73.8	10.9	3.5	1057.4	40	21.5	76.3	10.2	3.5	816.5	40	21.10	79.10	9.98	3.07	464.84	-6.19%	-2.59%	-22.78%	0	-8.44%	-12.29%	-56.04%

	N3 I	POR		tio	Ratio (MPW Opt/ N3)		
ULVT	Speed (GHz)	Leakage (nW)	Speed	pt/ N3) Leakage	Speed	Leakage	
MB4LHQ_NOM4222_D1_143MH286	10.5	257.09	6.67%	81.22%	5.62%	4.00%	
MB6LHQ_NOM4222_D1_143MH286	9.7	361.98	10.31%	77.14%	8.45%	1.24%	
MB8LHQ_NOM4222_D1_143MH286	9.1	466.82	12.09%	74.91%	9.67%	-0.42%	

() a navenu	Sim Va	D.,	
Cell (LVTLL)	Corner	3 Sigma	Bit
MB4LHQ_NOM4222_D1_143MH286	0.320	1.348	Q1
MB4LHQ_NOM4222_D1_143MH286(MPW Opt)	0.263	0.780	Q1
MB6LHQ_NOM4222_D1_143MH286	0.353	1.525	Q1
MB6LHQ_NOM4222_D1_143MH286(MPW Opt)	0.239	0.685	Q1
MB8LHQ_NOM4222_D1_143MH286	0.375	1.260	Q1
MB8LHQ_NOM4222_D1_143MH286(MPW Opt)	0.321	0.724	Q1

RC: Qcap C651 benchmark

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-Timing slew:INVDx-predriver, -cload: INVDx-FO4 @ SSGNP/0.5V/m25c for PPA

-power slew: INVDx-predriver, -cload: 0.001fF @ FFGNP/0.75V/85C

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